

Photo DMOS-FET Relay

Description

The **LU634** is a 1-Form B solid state relay in a 4 pin SMD package that employs optically coupled MOSFET technology to provide 3750V/5000V of input to output isolation. The optically coupled input is controlled by a highly efficient GaAlAs infrared LED and MOS FETs on the output side.

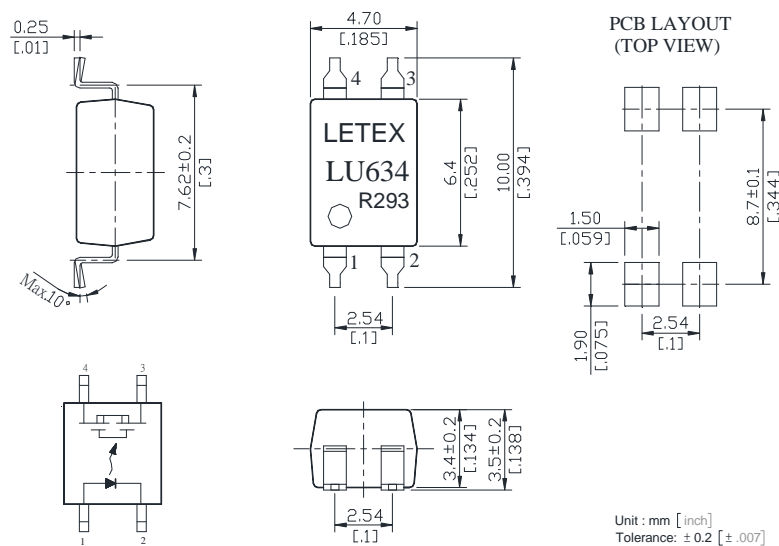
Features

- Low driver power requirements (TTL/CMOS Compatible)
- Contact form: Normally-On (1b)
- Load voltage: 60V max.
- On-Resistance: 3Ω max.
- 3750 / 5000 Vrms Input/Output isolation
- Tape & Reel version available

Applications

- Telecommunications (PC, Electronic notepad)
- Measuring and Testing equipment
- Industrial control
- Security equipments
- High speed inspection machine

Outline Dimensions



1. LED Anode
2. LED Cathode
3. Drain (MOS FET)
4. Drain (MOS FET)

Photo DMOS-FET Relay Specifications

Part Name: LU634

(Load voltage: 60V / Load current: 500mA)

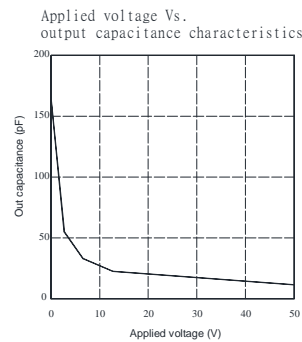
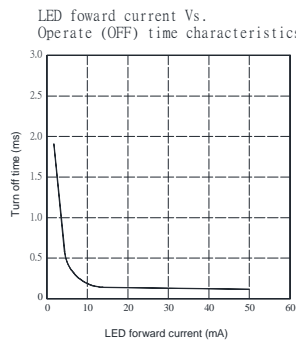
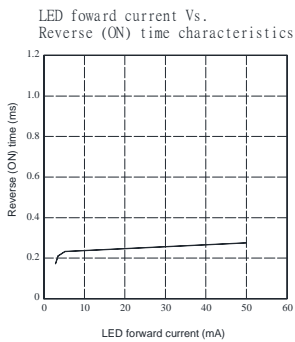
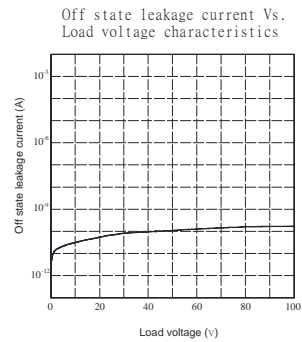
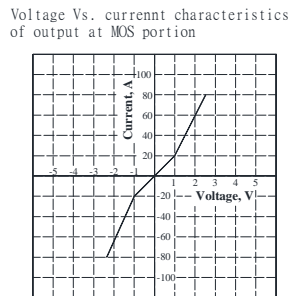
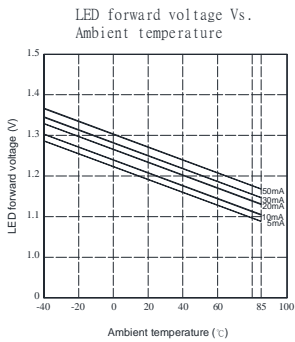
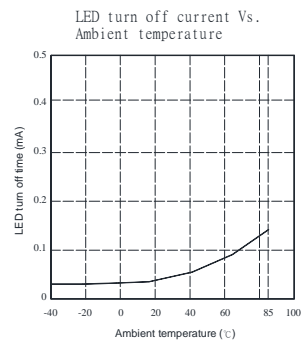
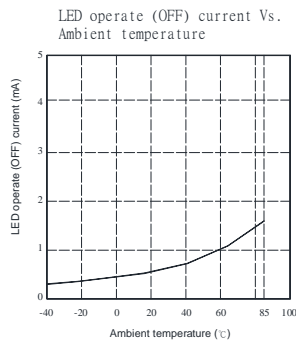
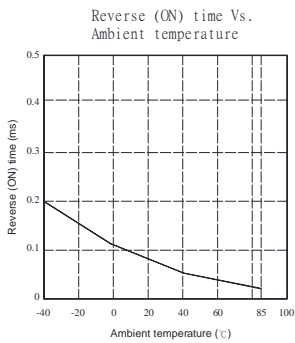
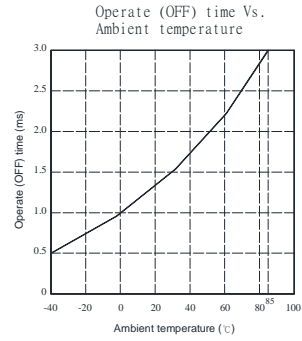
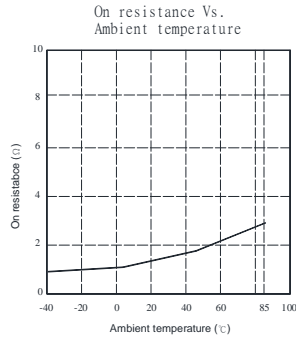
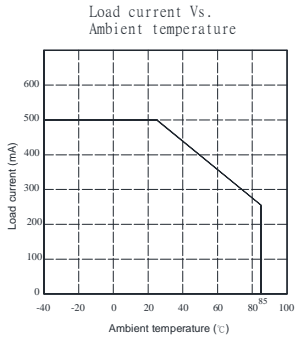
Absolute Maximum Ratings (Ambient Temperature: 25°C)

Item		Symbol	Value	Units	Note
Input	Continuous LED Current	IF	50	mA	
	Peak LED Current	IFP	1000	mA	f=100Hz, duty=1%
	LED Reverse Voltage	VR	5	V	
	Input Power Dissipation	PIn	75	mW	
Output	Load Voltage	VL	60	V(AC peak or DC)	
	Load Current	IL	500	mA	
	Peak Load Current	IPeak	0.6	A	1ms(1 pulse)
	Output Power Dissipation	Pout	300	mW	
Total Power Dissipation		PT	350	mW	
I/O Breakdown Voltage		VI/O	3750	Vrms	RH=60%, 1min
I/O Breakdown Voltage(Suffix-V)		VI/O	5000	Vrms	RH=60%, 1min
Operating Temperature		Topr	-40 to +85	°C	
Storage Temperature		Tstg	-40 to +100	°C	
Pin Soldering Temperature		Tsol	260	°C	10 sec max.

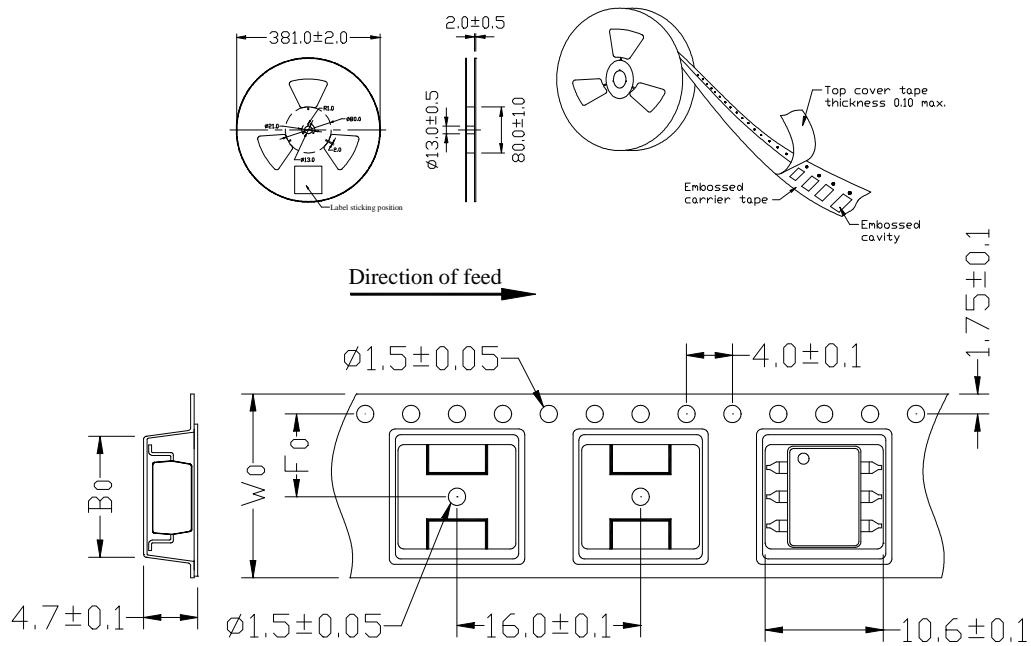
Electrical Specifications (Ambient Temperature: 25°C)

Item		Symbol	MIN.	TYP.	MAX.	Units	Conditions
Input	LED Forward Voltage	V _F		1.2	1.5	V	IF=10mA
	Operation LED Current	I _{Fon}		0.5	5.0	mA	
	Recovery LED Current	I _{Foff}	0.1	0.4		mA	
	Recovery LED Voltage	V _{Foff}	0.5			V	
Output	On-Resistance	R _{on}		1	3	Ω	IF=0mA,IL=100mA, Time to flow is within 1 sec.
	Off-State Leakage Current	I _{Leak}			1	uA	IF=10mA,VL=60V
	Output Capacitance	C _{out}		165		pF	IF=10mA,VL=0V, f=1MHz
Transmis sion	Turn-Off Time	T _{off}		0.5	3.0	ms	IF=10mA,
	Turn-On Time	T _{on}		0.25	1.0	ms	IL=100mA
Coupled	I/O Isolation Resistance	R _{I/O}	10 ¹⁰			Ω	DC500V
	I/O Capacitance	C _{I/O}		0.8		pF	f=1MHz

Reference Data



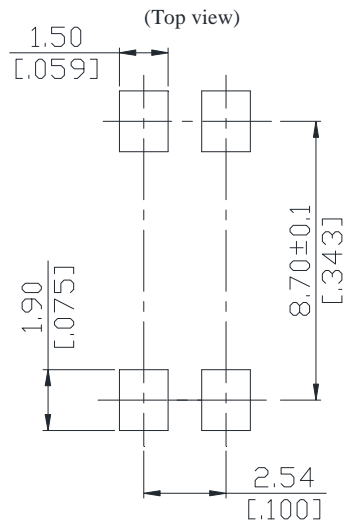
Taping Specifications for Surface Mount Devices



Unit: mm

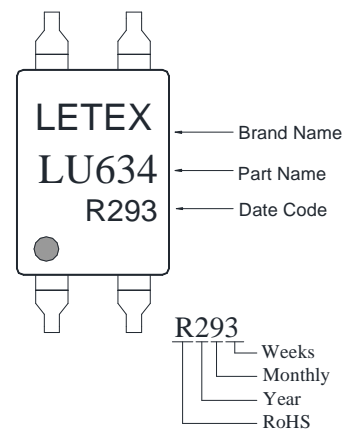
TYPE	B0±0.1	F0±0.1	W0±0.1	15" REEL/PCS
4P	5.3	7.5	16	1000

Recommended Mounting Pad



Marking

(Each photo MOS Relay shall be marked with the following information)



Unit : mm [inch]
Tolerance : ±0.1

- Note:
1. There shall be leader of 230 mm minimum which may consist of carrier and or cover tape follower by a minimum of 160 mm of carrier tape sealed with cover tape.
 2. There shall be a minimum of 160 mm of empty component pockets sealed with cover tape.
 3. Devices are pockets in accordance with EIA standard EIA-481-A and specifications given above.